

# **TMR2105**

Large Dynamic Range TMR Linear Sensor

### **General Description**

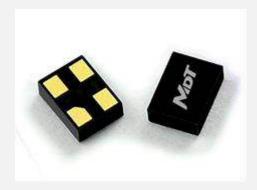
The TMR2105 linear sensor utilizes a unique push-pull Wheatstone bridge composed of four unshielded TMR sensor elements. The unique bridge design provides a high sensitivity differential output that is linearly proportional to a magnetic field applied parallel to the surface of the sensor package, and it provides superior temperature compensation of the output. The TMR2105 is available in a 2 mm X1.5 mm X 0.73 mm LGA4 package.

#### **Features and Benefits**

- Tunneling Magneto resistance (TMR) Technology
- Large Dynamic Range up to 1000 Oe
- Low Power Consumption
- Excellent Thermal Stability

### **Applications**

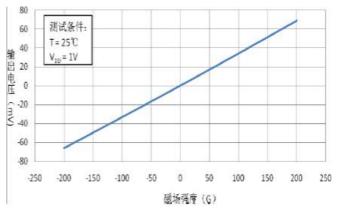
- Magnetic Field Sensing
- Current Sensors
- Displacement Sensing
- Rotary Position Sensors

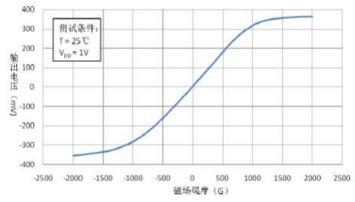


TMR2105

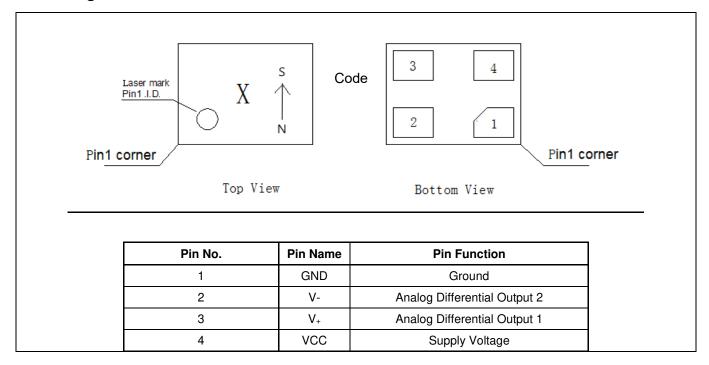
#### **Transfer Curve**

The following figure shows the response of the TMR2105 to an applied magnetic field in the range of ±200 Oe (left) and ±2000 Oe (right) when the TMR2105 is biased at 1 V.





### **Pin Configuration**



# **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit	
Supply Voltage	Vcc	7	V	
Reverse Supply Voltage	V <sub>RCC</sub>	7	V	
Magnetic Field	Н	1500	Oe <sup>(1)</sup>	
ESD Voltage	$V_{ESD}$	4000	V	
Operating Temperature	TA	-40~125	°C	
Storage Temperature	T <sub>stg</sub>	-50 ~150	°C	

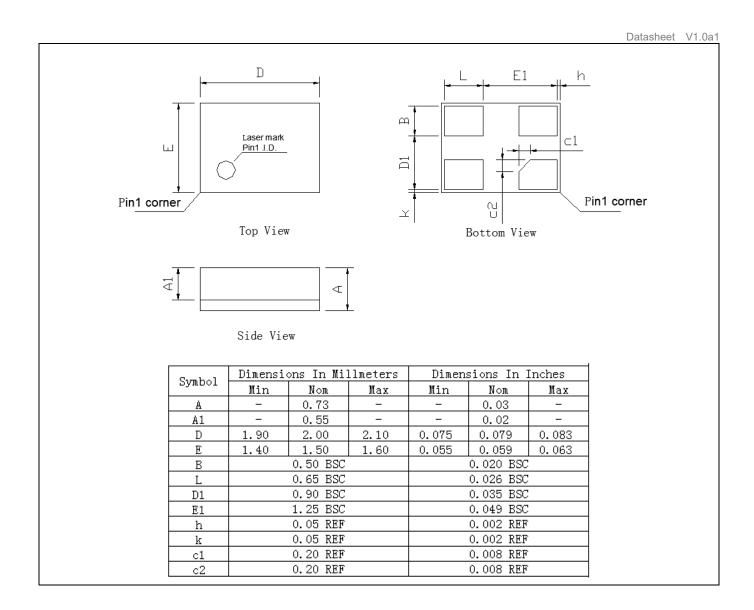
## Specification (V<sub>CC</sub>=1.0V, T<sub>A</sub>=25°C, Differential Output)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Supply Voltage	Vcc	Operating		1	7	V
Supply Current	Icc	Output Open		16 <sup>(2)</sup>		μA
Resistance(SOP8)	R			60 <sup>(2)</sup>		KOhm
Sensitivity	SEN	Fit @±150 Oe		0.3		mV/V/Oe
Saturation Field	H <sub>sat</sub>			±1000		Oe
Non-Linearity	NONL	Fit @±150 Oe		0.1		%FS
Offset Voltage	V <sub>offset</sub>		-10		10	mV/V
Hysteresis	Hys	Fit @±150 Oe		1.5		Oe
Temperature Coefficient of Resistance	TCR	H = 0 Oe		-600		PPM/°C
Temperature Coefficient of Sensitive	TCS			-300		PPM/°C

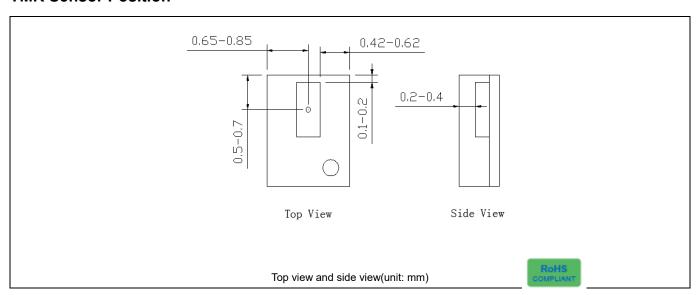
Notes:

- (1) 1 Oe (Oersted) = 1 Gauss in air = 0.1 millitesla = 79.8 A/m.
- (2) Custom resistance may be available upon request.

## **Package Information**



#### **TMR Sensor Position**





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